

Silicon PNP Power Transistors

2SA1094

DESCRIPTION

- With MT-200 package
- Complement to type 2SC2564

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

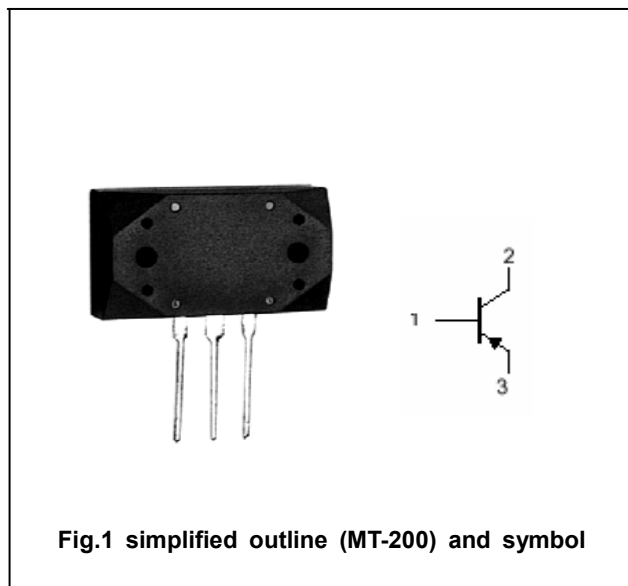


Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-140	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-140	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-12	A
I <sub>B</sub>	Base current		-1.2	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	120	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -0.1A ; I_B = 0$	-140			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -0.01A ; I_C = 0$	-5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = -5A ; I_B = -0.5A$			-2.0	V
$V_{BE}$	Base-emitter on voltage	$I_C = -5A ; V_{CE} = -5V$			-2.0	V
$I_{CBO}$	Collector cut-off current	$V_{CB} = -140V ; I_E = 0$			-50	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -5V ; I_C = 0$			-50	$\mu A$
$h_{FE-1}$	DC current gain	$I_C = -1A ; V_{CE} = -5V$	55		240	
$h_{FE-2}$	DC current gain	$I_C = -5A ; V_{CE} = -5V$	30			
$C_{ob}$	Output capacitance	$I_E = 0 ; V_{CB} = -10V ; f = 1MHz$		220		pF
$f_T$	Transition frequency	$I_C = -1A ; V_{CE} = -10V$		70		MHz

◆  $h_{FE-1}$  classifications

R	O	Y
55-110	80-160	120-240

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PACKAGE OUTLINE

